



1NM80-Q

Preliminary

Power MOSFET

1.0A, 800V N-CHANNEL SUPER-JUNCTION MOSFET

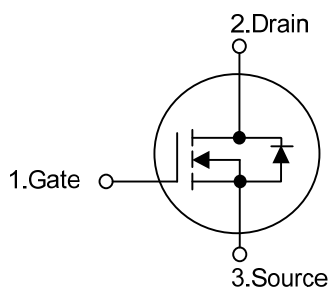
DESCRIPTION

The **UTC 1NM80-Q** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at AC-DC converters for power applications.

FEATURES

- * $R_{DS(ON)} \leq 4.3 \Omega$ @ $V_{GS}=10V$, $I_D=0.5A$
- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness

SYMBOL

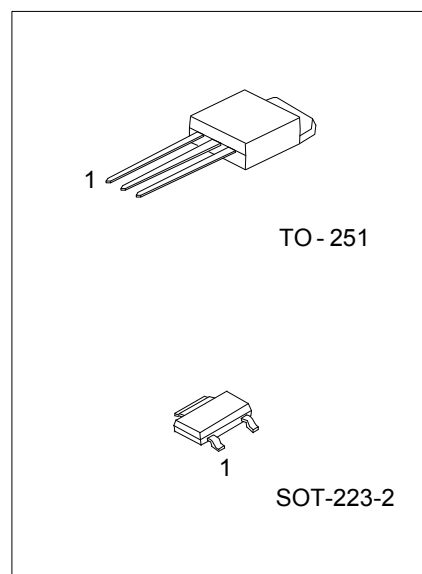


ORDERING INFORMATION

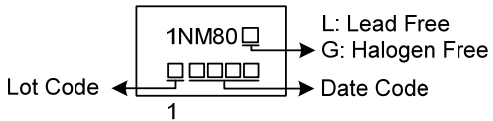
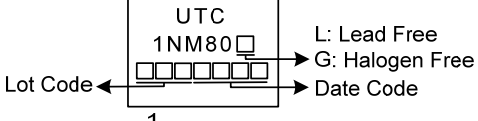
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
1NM80L-AA2-R	1NM80G-AA2-R	SOT-223-2	G	D	S	Tape Reel
1NM80L-TM3-T	1NM80G-TM3-T	TO-251	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

1NM80G-AA2-R	(1)Packing Type	(1) R: Tape Reel, T: Tube
	(2)Package Type	(2) AA2: SOT-223-2, TM3: TO-251
	(3)Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free



■ MARKING

SOT-223-2	TO-251
 Diagram of SOT-223-2 marking: A rectangular package with '1NM80' and a small square symbol on the top surface. Below the package, four small squares represent the Lot Code, and four small squares represent the Date Code. Arrows point from the Lot Code and Date Code to the package. To the right of the package, 'L: Lead Free' and 'G: Halogen Free' are listed. A '1' is printed below the package.	 Diagram of TO-251 marking: A cylindrical package with 'UTC' and '1NM80' and a small square symbol on the top surface. Below the package, four small squares represent the Lot Code, and four small squares represent the Date Code. Arrows point from the Lot Code and Date Code to the package. To the right of the package, 'L: Lead Free' and 'G: Halogen Free' are listed. A '1' is printed below the package.

■ **ABSOLUTE MAXIMUM RATINGS** ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	800	V
Gate-Source Voltage		V_{GSS}	± 30	V
Continuous Drain Current	Continuous	I_D	1	A
Pulsed Drain Current	Pulsed (Note 2)	I_{DM}	2	A
Single Pulsed Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	40	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	3.3	V/ns
Power Dissipation	SOT-223-2	P_D	1.2	W
	TO-251		10	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 100\text{mH}$, $I_{AS} = 0.9\text{A}$, $V_{DD} = 90\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$.

4. $I_{SD} \leq 1.0\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$.

■ **THERMAL DATA**

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	SOT-223-2	θ_{JA}	150	$^\circ\text{C}/\text{W}$
	TO-251		110	$^\circ\text{C}/\text{W}$
Junction to Case	SOT-223-2	θ_{JC}	104	$^\circ\text{C}/\text{W}$
	TO-251		12.5	$^\circ\text{C}/\text{W}$

Note: Device mounted on FR-4 substrate P_C board, 2oz copper, with 1inch square copper plate.

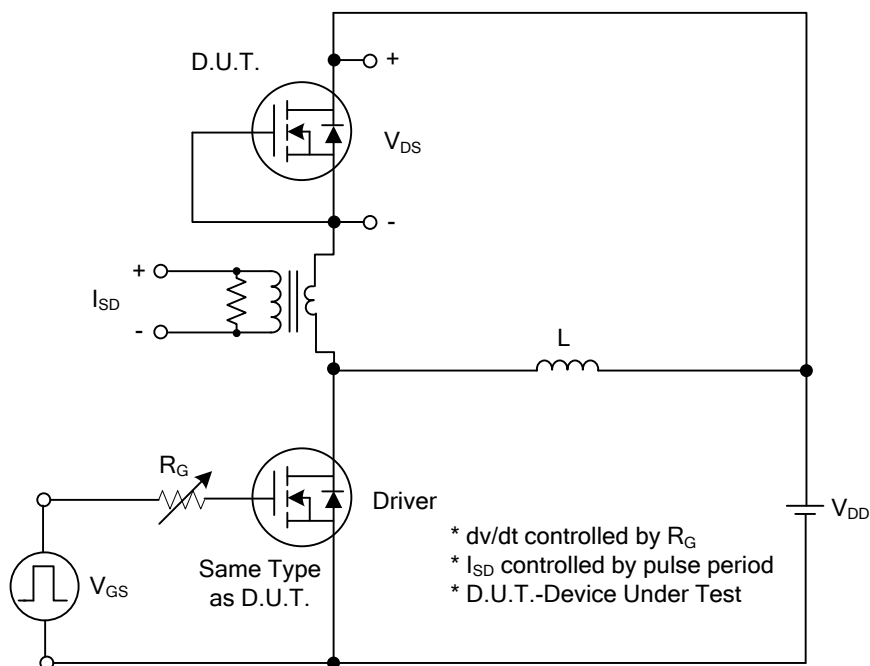
■ **ELECTRICAL CHARACTERISTICS** ($T_J=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V, I _D =250μA	800			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =800V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} =30V, V _{DS} =0V			100	nA
	Reverse		V _{GS} =-30V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.5		4.5	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =0.5A			4.3	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =50V, f=1.0MHz		125		pF
Output Capacitance		C _{OSS}			20		pF
Reverse Transfer Capacitance		C _{RSS}			2.3		pF
SWITCHING CHARACTERISTICS							
Total Gate Charge (Note 1)		Q _G	V _{DS} =640V, V _{GS} =10V, I _D =1.0A (Note 1, 2)		13		nC
Gate to Source Charge		Q _{GS}			4.5		nC
Gate to Drain Charge		Q _{GD}			2.2		nC
Turn-ON Delay Time (Note 1)		t _{D(ON)}	V _{DS} =100V, V _{GS} =10V, I _D =1.0A, R _G =25Ω (Note 1, 2)		4		nS
Rise Time		t _R			17		nS
Turn-OFF Delay Time		t _{D(OFF)}			25		nS
Fall-Time		t _F			52		nS
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Continuous Drain-Source Diode Forward Current		I _S				1	A
Maximum Pulsed Drain-Source Diode Forward Current		I _{SM}				2	A
Drain-Source Diode Forward Voltage (Note 1)		V _{SD}	I _S =1.0A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)		t _{rr}	I _S =1.0A, V _{GS} =0V,		195		nS
Body Diode Reverse Recovery Charge		Q _{rr}	dl _F /dt=100A/μs		575		nC

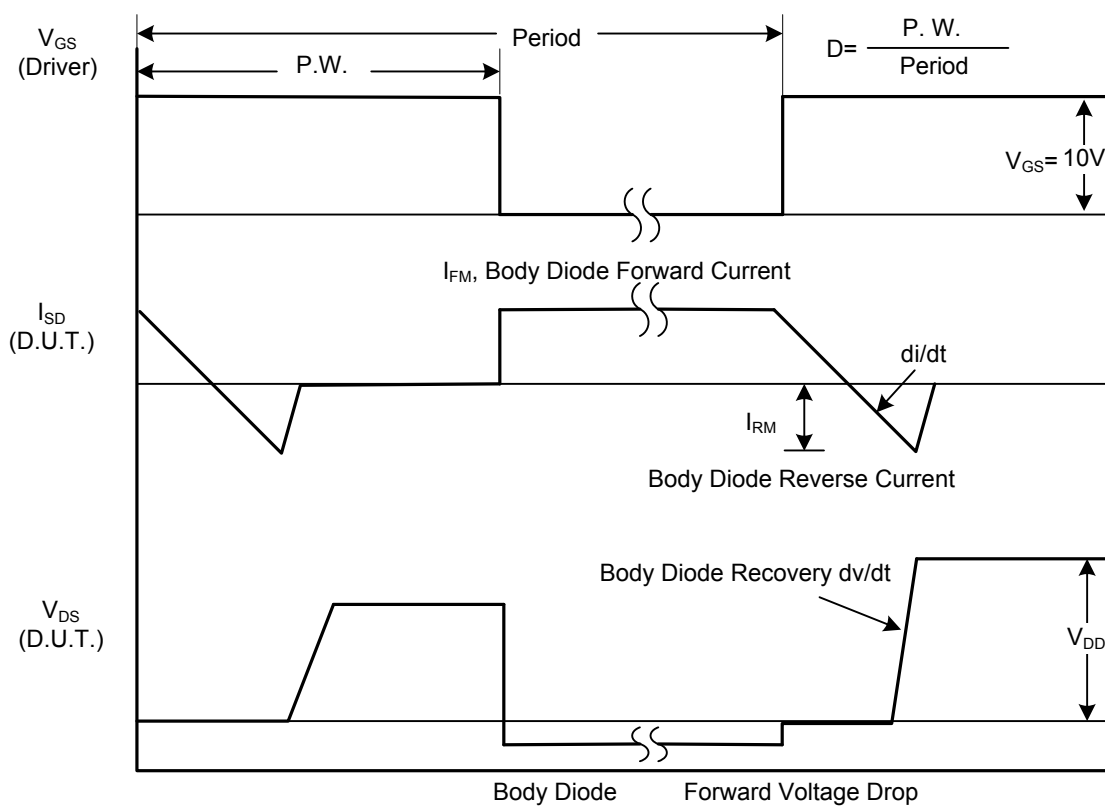
Notes: 1. Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating ambient temperature.

■ TEST CIRCUITS AND WAVEFORMS

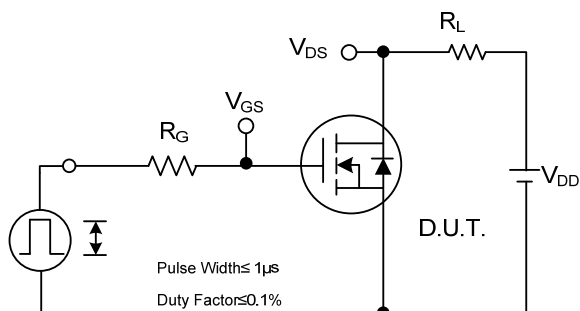


Peak Diode Recovery dv/dt Test Circuit

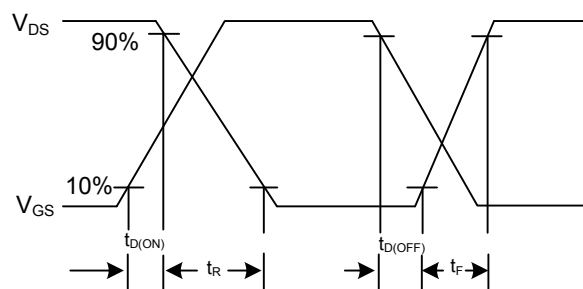


Peak Diode Recovery dv/dt Waveforms

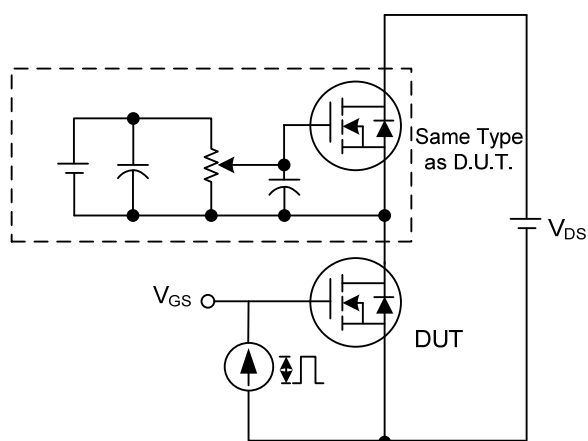
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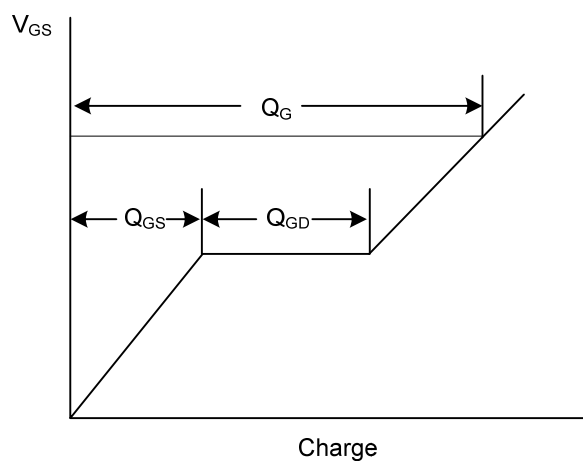
Switching Test Circuit



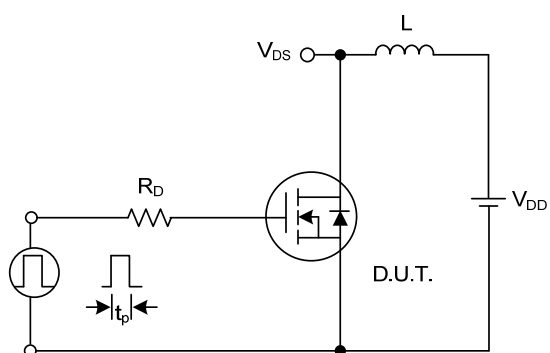
Switching Waveforms



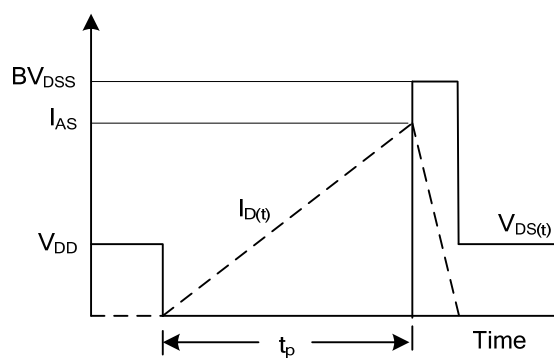
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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